



General Description

The AO4455 uses advanced trench technology to provide excellent $R_{DS(ON)}$, and ultra-low gate charge with a 25V gate rating. This device is suitable for use as a load switch or in PWM applications.

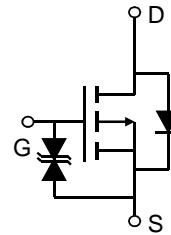
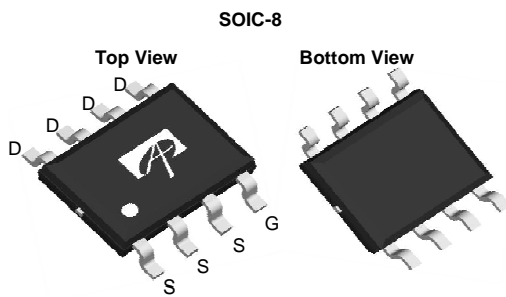
* RoHS and Halogen-Free Compliant

Product Summary

V_{DS} (V) = -30V
 I_D = -17A
 $R_{DS(ON)} < 6.2m\Omega$
 $R_{DS(ON)} < 7.2m\Omega$

($V_{GS} = -20V$)
($V_{GS} = -20V$)
($V_{GS} = -10V$)

ESD Protected
100% UIS tested
100% Rg tested



Absolute Maximum Ratings $T_A=25^\circ\text{C}$ unless otherwise noted

Parameter	Symbol	Maximum	Units
Drain-Source Voltage	V_{DS}	-30	V
Gate-Source Voltage	V_{GS}	± 25	V
Continuous Drain Current ^{AF}	I_D	$T_A=25^\circ\text{C}$	-17
		$T_A=70^\circ\text{C}$	-14
Pulsed Drain Current ^B	I_{DM}	-182	A
Power Dissipation ^A	P_D	$T_A=25^\circ\text{C}$	3.1
		$T_A=70^\circ\text{C}$	2
Junction and Storage Temperature Range	T_J, T_{STG}	-55 to 150	$^\circ\text{C}$

Thermal Characteristics

Parameter	Symbol	Typ	Max	Units
Maximum Junction-to-Ambient ^{AF}	$R_{\theta JA}$	$t \leq 10s$	26	$^\circ\text{C/W}$
Maximum Junction-to-Ambient ^A		Steady-State	50	$^\circ\text{C/W}$
Maximum Junction-to-Lead ^C	$R_{\theta JL}$	14	24	$^\circ\text{C/W}$

Electrical Characteristics (T_J=25°C unless otherwise noted)

Symbol	Parameter	Conditions	Min	Typ	Max	Units
STATIC PARAMETERS						
BV _{DSS}	Drain-Source Breakdown Voltage	I _D =-250μA, V _{GS} =0V	-30			V
I _{DSS}	Zero Gate Voltage Drain Current	V _{DS} =-30V, V _{GS} =0V T _J =55°C			-1 -5	μA
I _{GSS}	Gate-Body leakage current	V _{DS} =0V, V _{GS} =±20V			±1	μA
		V _{DS} =0V, V _{GS} =±25V			±10	μA
V _{GS(th)}	Gate Threshold Voltage	V _{DS} =V _{GS} , I _D =-250μA	-1.5	-2.1	-2.6	V
R _{DS(ON)}	Static Drain-Source On-Resistance	V _{GS} =-20V, I _D =-15A T _J =125°C		5 7.2	6.2 9	mΩ
		V _{GS} =-10V, I _D =-15A		5.7	7.2	mΩ
		V _{GS} =-6V, I _D =-10A		7.4	9.5	mΩ
g _{FS}	Forward Transconductance	V _{DS} =-5V, I _D =-15A		48		S
V _{SD}	Diode Forward Voltage	I _S =-1A, V _{GS} =0V		-0.7	-1	V
I _S	Maximum Body-Diode Continuous Current				-4.2	A
DYNAMIC PARAMETERS						
C _{iss}	Input Capacitance			2823	3400	pF
C _{oss}	Output Capacitance	V _{GS} =0V, V _{DS} =-15V, f=1MHz		574		pF
C _{riss}	Reverse Transfer Capacitance			424	600	pF
R _g	Gate resistance	V _{GS} =0V, V _{DS} =0V, f=1MHz	2.1	4.0	6.4	Ω
SWITCHING PARAMETERS						
Q _g	Total Gate Charge			54	76	nC
Q _{gs}	Gate Source Charge	V _{GS} =-10V, V _{DS} =-15V, I _D =-15A		9		nC
Q _{gd}	Gate Drain Charge			16		nC
t _{D(on)}	Turn-On Delay Time			12.5		ns
t _r	Turn-On Rise Time	V _{GS} =-10V, V _{DS} =-15V, R _L =1.0Ω,		12.5		ns
t _{D(off)}	Turn-Off Delay Time	R _{GEN} =3Ω		49		ns
t _f	Turn-Off Fall Time			109		ns
t _{rr}	Body Diode Reverse Recovery Time	I _F =-15A, dI/dt=100A/μs		22.3	32	ns
Q _{rr}	Body Diode Reverse Recovery Charge	I _F =-15A, dI/dt=100A/μs		8.8		nC

A: The value of R_{θJA} is measured with the device mounted on 1in 2 FR-4 board with 2oz. Copper, in a still air environment with T_A=25° C. The value in any given application depends on the user's specific board design.

B: Repetitive rating, pulse width limited by junction temperature.

C: The R_{θJA} is the sum of the thermal impedance from junction to lead R_{θJL} and lead to ambient.

D: The static characteristics in Figures 1 to 6 are obtained using <300 μs pulses, duty cycle 0.5% max.

E: These tests are performed with the device mounted on 1 in 2 FR-4 board with 2oz. Copper, in a still air environment with T_A=25° C. The SOA curve provides a single pulse rating.

F: The current rating is based on the t ≤ 10s junction to ambient thermal resistance rating.

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TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS

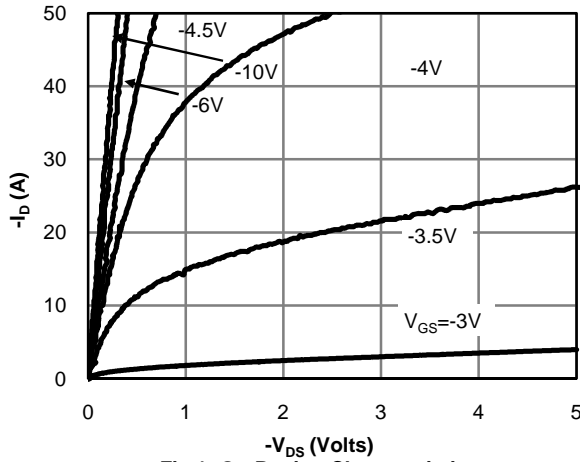


Fig 1: On-Region Characteristics

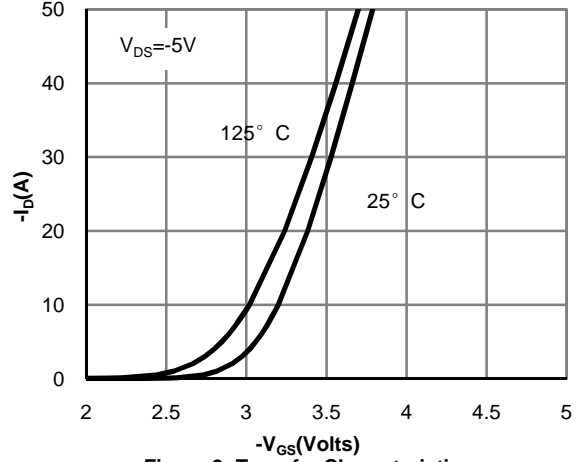


Figure 2: Transfer Characteristics

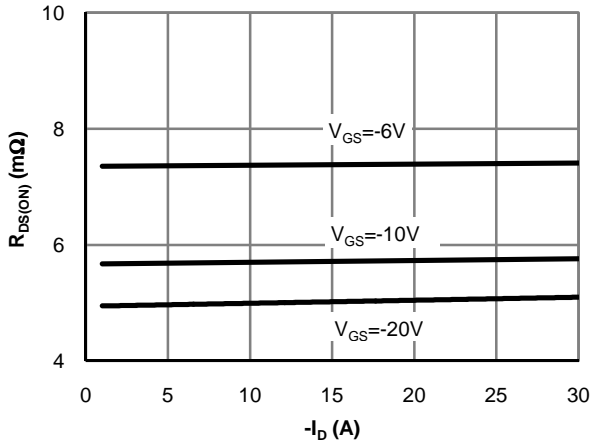


Figure 3: On-Resistance vs. Drain Current and Gate Voltage

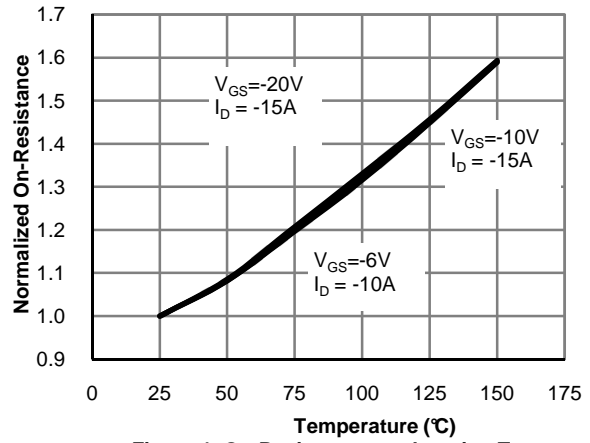


Figure 4: On-Resistance vs. Junction Temperature

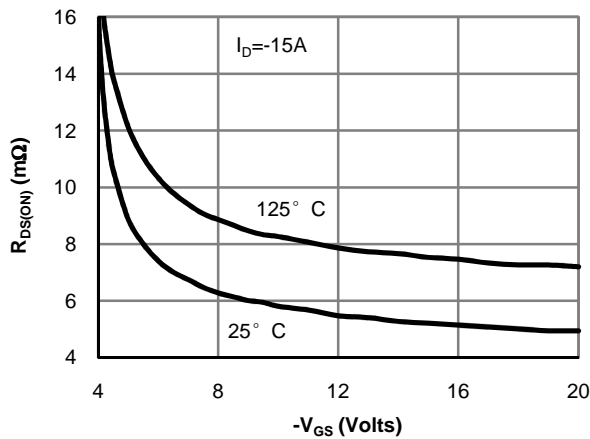


Figure 5: On-Resistance vs. Gate-Source Voltage

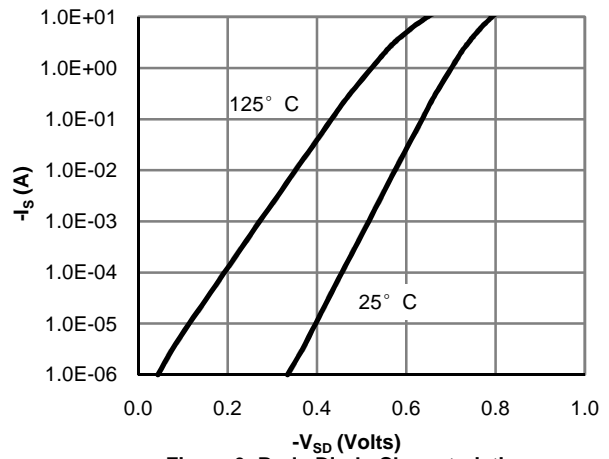


Figure 6: Body-Diode Characteristics

TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS

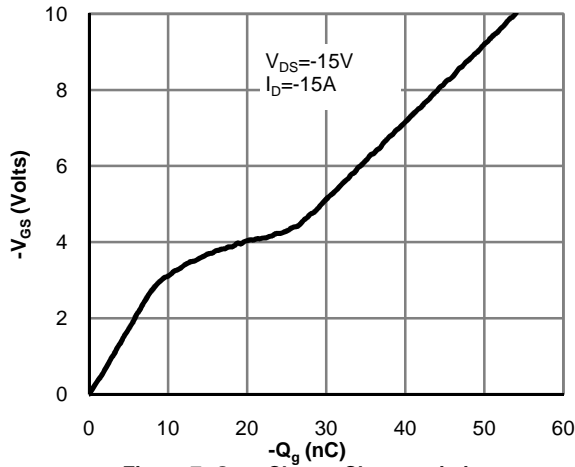


Figure 7: Gate-Charge Characteristics

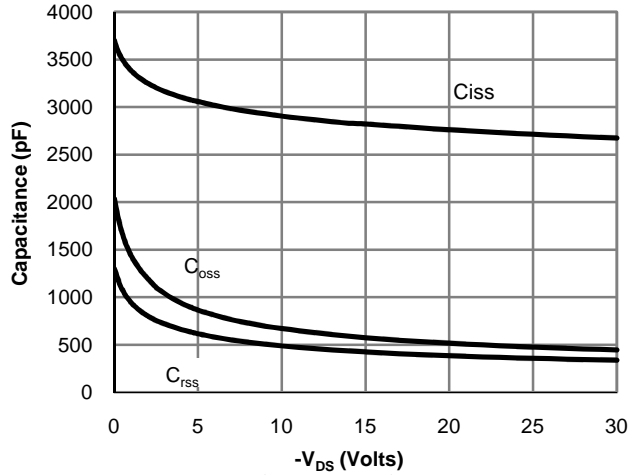


Figure 8: Capacitance Characteristics

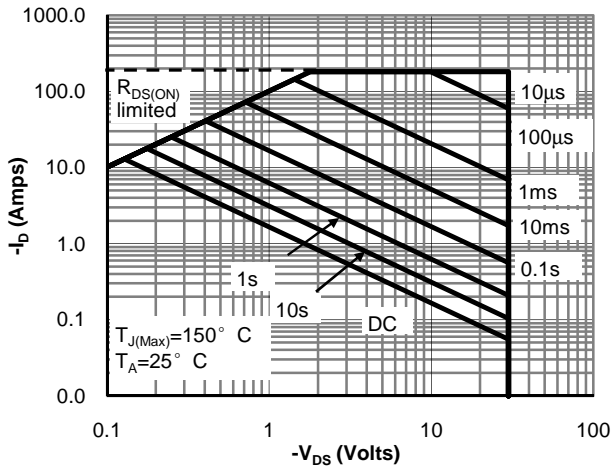


Figure 9: Maximum Forward Biased Safe

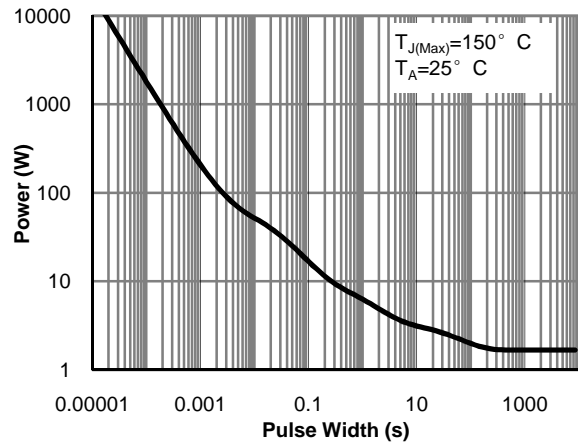


Figure 10: Single Pulse Power Rating Junction-to-Ambient (NOTE E)

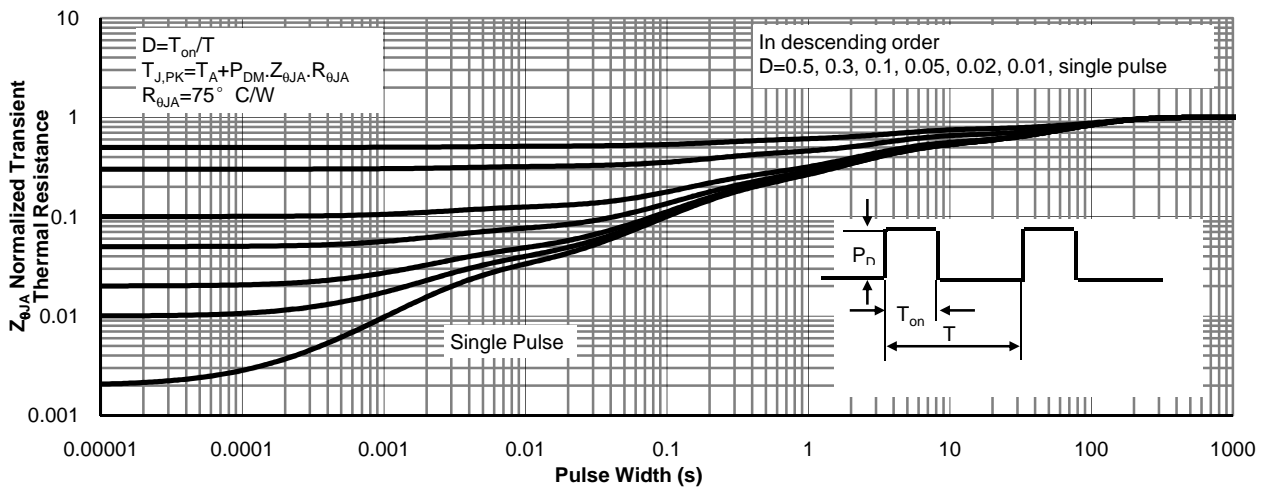
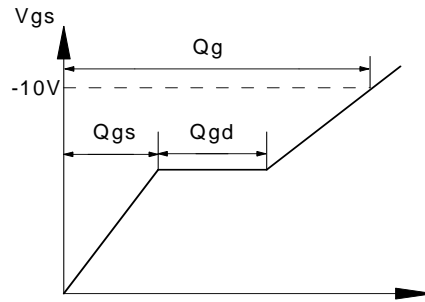
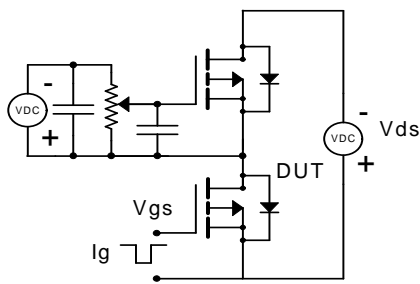
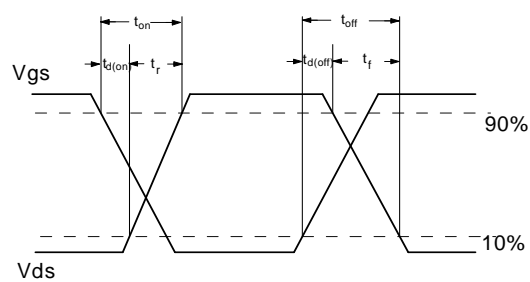
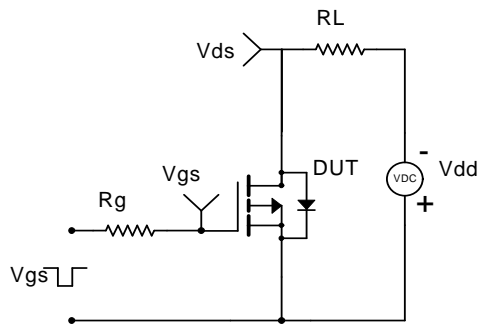


Figure 11: Normalized Maximum Transient Thermal Impedance

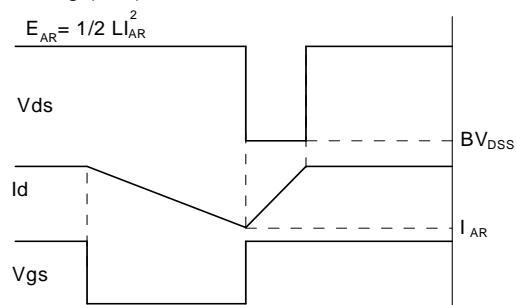
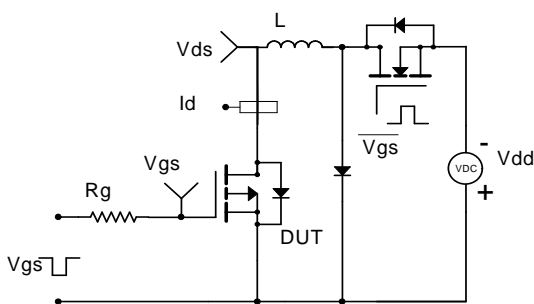
Gate Charge Test Circuit & Waveform



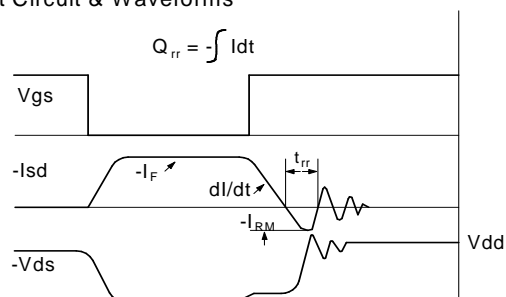
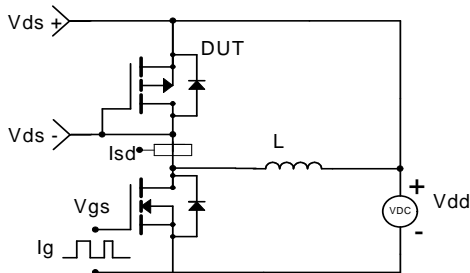
Resistive Switching Test Circuit & Waveforms



Unclamped Inductive Switching (UIS) Test Circuit & Waveforms



Diode Recovery Test Circuit & Waveforms



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